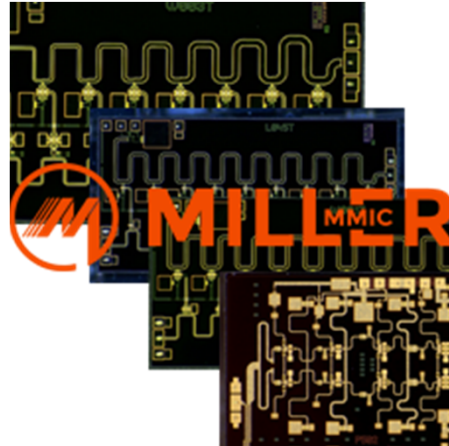


Features

- SP2T Reflective design
- Frequency:DC~4GHz
- Isolation: 55dB
- Insertion Loss: 0.5dB
- Return Loss (ON):15dB
- Control Voltage:0/-5V
- Switching Speed: 15 ns
- Die Size: 0.9x0.92x 0.1 mm

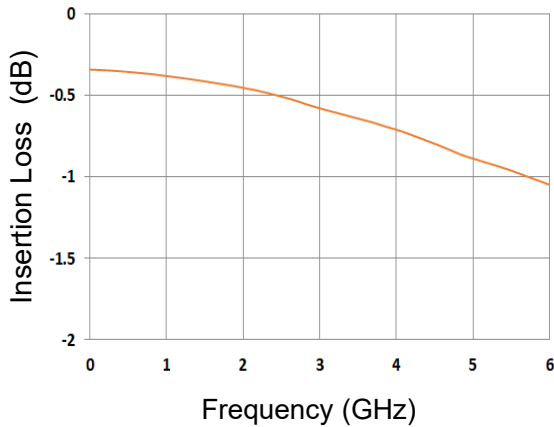

Typical Applications

- Voltage control no current
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Customization available upon request

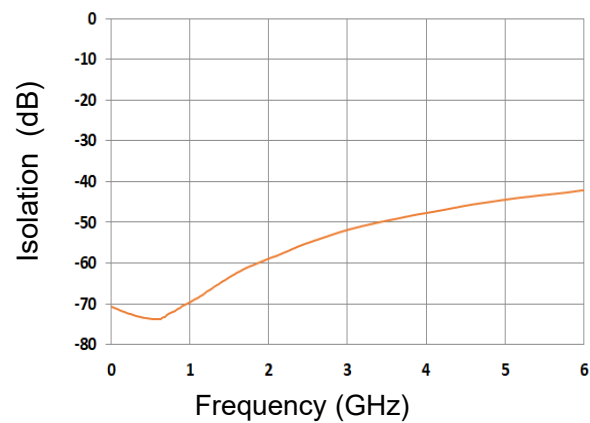
Electrical Specifications
TA = +25°C, VCTL=0/-5V

Parameters	Min.	Typ.	Max.	Units
Frequency	DC~4			GHz
Insertion Loss		0.5	0.8	dB
Isolation	45	55		dB
Return Loss (ON State)	13	20		dB
Input P-1		27		dBm
RF Input power			30	dBm
IIP3		32		dBm
Switching Speed	15			ns

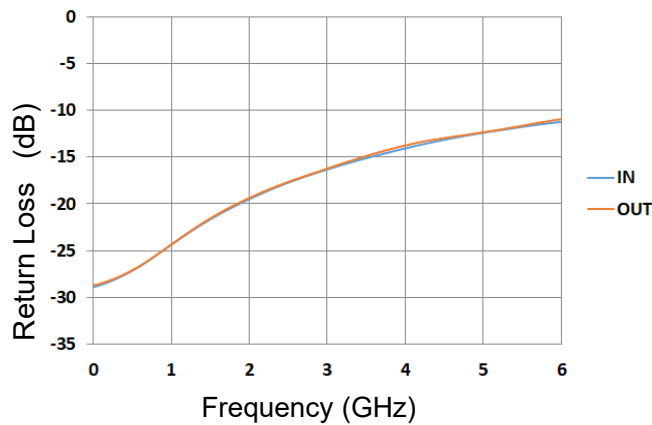
Insertion Loss @25°C



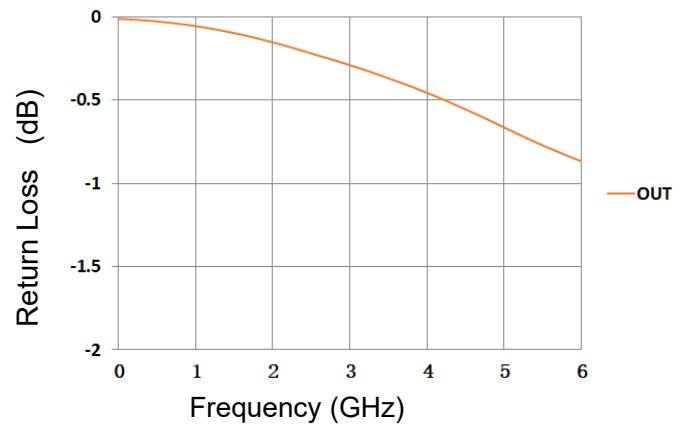
Isolation @25°C



Return Loss (ON) @25°C



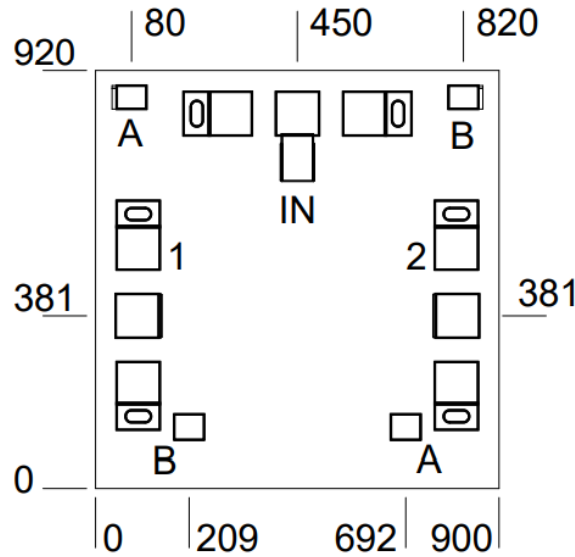
Output Return Loss (OFF) @25°C





Outline Drawing:

All Dimensions in mm

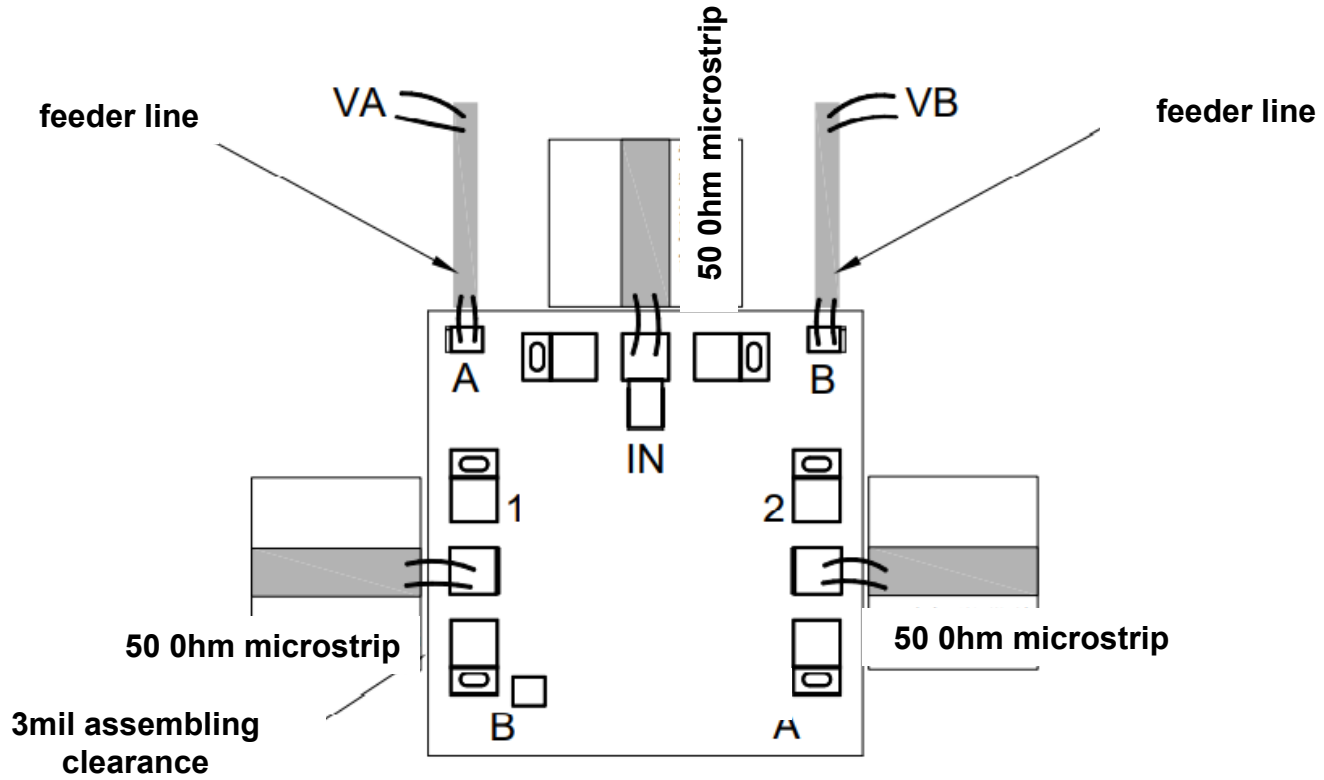


True Table

A	B	IN-1	IN-2
-5	0	ON	OFF
-0	-5	OFF	ON



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +30dBm
2. Control Voltage: -8~+1V
3. Storage temperature: -65°C to +150°C
4. Operating temperature: -55°C to 125°C